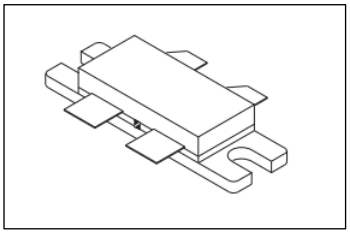
MK0160VPXF LDMOS TRANSISTOR

Preliminary Datasheet V1.0

600W, HF-0.5GHz 50V High Power RF LDMOS



Description

The MK0160VPXF is a 600W Push Pull 50V LDMOS, unmatched for any applications within HF-0.5GHz。It supports CW, and pulsed and any modulated signal at either saturated or linear application.

It can marginally be the drop-in replacement of its equivalent 300-400W VDMOS like BLF278/MRF151G/VRF151G with higher efficiency, improved thermal performance and stability.

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Suitable Applications

- 30-88MHz (Ground communication)
- 54-88MHz (TV VHF I)
- 88-108MHz (FM)
- 160-230MHz (TV VHF III)
- 136-174MHz (Commercial ground communication)
- Laser Exciter
- Synchrotron
- MRI
- Plasma generator
- Weather Radar

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	+135	Vdc
Gate--Source Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+55	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T_C= 85°C, T_J=200°C, DC test	$R_{\theta JC}$	TBD	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics (T_A = 25 ℃ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DC Characteristics (per half section)					
Drain-Source Voltage V_{GS}=0, I_{DS}=1.0Ma	$V_{(BR)DSS}$		135		V
Zero Gate Voltage Drain Leakage Current (V_{DS} = 75V, V_{GS} = 0 V)	I_{DSS}	——	——	1	μA

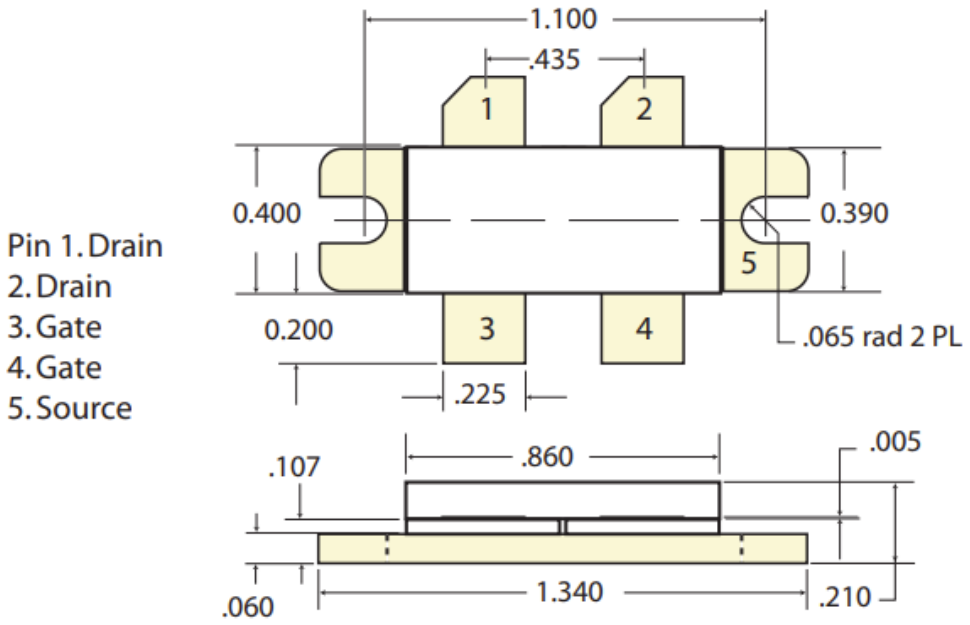
Zero Gate Voltage Drain Leakage Current (V_{DS} = 50 V, V_{GS} = 0 V)	I_{DSS}	——	——	1	μA
Gate--Source Leakage Current (V_{GS} = 10 V, V_{DS} = 0 V)	I_{GSS}	——	——	1	μA
Gate Threshold Voltage (V_{DS} = 50V, I_D = 600 μA)	$V_{GS(th)}$	——	2.65	——	V
Gate Quiescent Voltage (V_{DD} = 50 V, I_D = 300 mA, Measured in Functional Test)	$V_{GS(Q)}$	——	3.44	——	V
Drain source on state resistance (Vds=0.1V, Vgs=10V)	Rds(on)		260		mΩ
Common Source Input Capacitance (V_{GS} = 0V, V_{DS} =50 V, f = 1 MHz)	C_{ISS}		305		pF
Common Source Output Capacitance (V_{GS} = 0V, V_{DS} =50 V, f = 1 MHz)	C_{OSS}		68		pF
Common Source Feedback Capacitance (V_{GS} = 0V, V_{DS} =50 V, f = 1 MHz)	C_{RSS}		1.4		pF

Load Mismatch (In Innogration Test Fixture, 50 ohm system): V_{DD} = 50 Vdc, I_{DQ} = 300 mA, f = 500MHz, pulse width:100us, duty cycle:10%

Load 10:1 All phase angles, at 350W Pulsed CW Output Power	No Device Degradation

Package Outline

Flanged ceramic package;



Package Dimensions (inches)
All Dimensions are ± .005

Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2025/12/25	Rev 1.0	Preliminary datasheet

Application data based on

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